

2--200 MHz VHF AM/FM FETs

These RF TMOS Field-Effect Transistors are designed for VHF military and commercial aircraft radio transmitters. These transistors are fully characterized at 150 MHz.

Device	P _{out} Output Power Watts	P _{in} Input Power Watts	G _{ps} Minimum Gain dB	η Minimum Efficiency %	V _{DD} Supply Voltage	Package
MRF134	5.0	0.40	11	50	28	211-07
MRF136	15	0.75	13	50	28	211-07
MRF137	30	1.9	12	50	28	211-07
MRF171	45	2.8	12	50	28	211-07
MRF172	80	8.0	10	50	28	211-11
MRF174	125	15.8	9.0	50	28	211-11

2--400 MHz VHF/UHF AM/FM FETs

These RF TMOS Field-Effect Transistors are designed for VHF/UHF military and commercial aircraft radio transmitters. These transistors are fully characterized at 400 MHz.

Device	P _{out} Output Power Watts	P _{in} Input Power Watts	G _{ps} Minimum Gain dB	η Minimum Efficiency %	V _{DD} Supply Voltage	Package
MRF161	5.0	0.40	11	45	28	244-04
MRF162	15	1.2	11	45	28	244-04
MRF163	25	2.5	10	45	28	244-04